

## Technical Specifications



Solar Multicrystalline Wafer: 156mm x 156mm

<b>General Characteristics</b>	<b>Features</b>
Product	Multicrystalline silicon wafer
Growth Method	Directional solidification
Conductivity Type	P type
Dopant	Boron
Resistivity	0.5~2Ω.cm
Oxygen Content	$8 \times 10^{17}$ atom/cm <sup>3</sup>
Carbon Content	$5 \times 10^{16}$ atom/cm <sup>3</sup>
<b>Structural Characteristics</b>	<b>Features</b>
Side	156.0mm ± 0.5mm
Corner diagonal	1.5mm ± 0.5mm
Corner Angle	90°±0.3°
Thickness	200±20μm
Surface	No stain or splash on surface
<b>Mechanical Characteristics</b>	<b>Features</b>
TTV	≤50μm
Bow	≤60μm
Surface	No defect as cut , clean, free from stains, no cracks
Saw Mark	≤15μm